

FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 500466.02		APPLICATION NO. 09/994,511	
INFORMATION DISCLOSURE STATEMENT <i>(Use several sheets if necessary)</i>				APPLICANT(S) Kie Y Ahn; Leonard Forbes			
				FILING DATE November 26, 2001		GROUP ART UNIT 2879	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K/JN	AA	3,665,241	05/23/72	Spindt et al.	313	351	
K/JN	AB	3,755,704	08/28/73	Spindt et al.	313	309	
K/JN	AC	3,812,559	05/28/74	Spindt et al.	29	25	
K/JN	AD	4,266,233	05/05/81	Bertotti et al.	357	22	
K/JN	AE	5,142,184	8/25/92	Kane	313	309	
K/JN	AF	5,194,780	3/16/93	Meyer	315	169.3	
K/JN	AG	5,229,331	07/20/93	Doan et al.	437	228	
K/JN	AH	5,259,799	11/09/93	Doan et al.	445	24	
K/JN	AI	5,358,908	10/25/94	Reinberg et al.	437	228	
K/JN	AJ	5,372,973	12/13/94	Doan et al.	437	228	
K/JN	AK	5,483,067	01/09/96	Fujii et al.	250	338.3	
K/JN	AL	5,578,896	11/26/96	Huang	313	309	
K/JN	AM	5,585,301	12/17/96	Lee et al.	437	60	
K/JN	AN	5,597,444	01/28/97	Gilton	156	643	
K/JN	AO	5,653,619	08/05/97	Cloud et al.	445	24	
K/JN	AP	5,853,492	12/29/98	Cathey et al.	134	3	
K/JN	AQ	5,712,534	1/27/98	Lee et al.	315	169.3	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AR						
OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
K/JN	AS	Anderson, R.C. et al., "Porous Polycrystalline Silicon: A New Material for MEMS," <i>Journal of Microelectromechanical Systems</i> 3(1):10-18, 1994					
K/JN	AT	Boswell, E.C. et al., "Polycrystalline Silicon Field Emitters," 8 th International Vacuum Microelectronics Conference Technical Digest, pp. 181-186, 1996					
EXAMINER KENNETH J. RAMSEY PRIMARY EXAMINER				DATE CONSIDERED 10/24/03			
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K/A	BA	Boswell, E.C. et al., "Polycrystalline silicon field emitters," <i>J Vac Sci Technol. B</i> 14(3):1910-1913, 1996			
K/A	BB	Huang, W.N. et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching," <i>Semicond. Sci. Technol.</i> 12:228-233, 1997			
K/A	BC	Huang, W.N. et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering," <i>IEEE Hong Kong Electron Devices Meeting</i> , pp. 21-24, 1996			
K/A	BD	Huq, S.E. et al., "Comparative study of gated single crystal silicon and polysilicon field emitters," <i>J. Vac. Sci. Technol. B</i> 15(6):2855-2858, 1997			
K/A	BE	Huq, S.E. et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 367-370, 1996			
K/A	BF	Kim, I.H. et al., "Metal FEAs on Double Layer Structure of Polycrystalline Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 423-426, 1996			
K/A	BG	Kim, I.H. et al., "Fabrication of metal field emitter arrays on polycrystalline silicon," <i>J. Vac. Sci. Technol. B</i> 15(2):468-471, 1997			
K/A	BH	Ku, T.K. et al., "Enhanced Electron Emission from Phosphorus-Doped Diamond-Clad Silicon Field Emitter Arrays," <i>IEEE Electron Device Letters</i> 17(5):208-210, 1996			
K/A	BI	Lacher, F. et al., "Electron field emission from thin fine-grained CVD diamond films," <i>Diamond and Related Materials</i> 6:1111-1116, 1997			
K/A	BJ	Lazarouk, S. et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon," <i>Journal of Non-Crystalline Solids</i> 198-200:973-976, 1996			
K/A	BK	Lee, J.H. et al., "A New Fabrication Method of Silicon Field Emitter Array with Local Oxidation of Polysilicon and Chemical-Mechanical-Polishing," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 415-418, 1996			
K/A	BL	Lee, K.R. et al., "Field emission behavior of (nitrogen incorporated) diamond-like carbon films," <i>Thin Solid Films</i> 290-291:171-175, 1996			
K/A	BM	Litovchenko, V.G. et al., "Emission Properties of the Silicon Cathodes Coated with Doped Diamond-Like Carbon Films," <i>IEEE International Conf. On Plasma Science</i> , p. 308, Abstract 7A02, 1997			
K/A	BN	Pullen, S.E. et al., "Enhanced Field Emission from Polysilicon Emitters Using Porous Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 211-214, 1996			
K/A	BO	Uh, H.S. et al., "Enhanced Electron Emission and Its Stability from Gated Mo-polycide Field Emitters," <i>IEEE</i> , pp. 713-716, 1997			
K/A	BP	Uh, H.S. et al., "Fabrication and Characterization of Gated n+ Polycrystalline Silicon Field Emitter Arrays," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 419-422, 1996			
K/A	BQ	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrays for flat-panel display applications," <i>J. Vac. Sci. Technol. B</i> 15(2):472-476, 1997			
K/A	BR	Vaudaine, P. and Meyer, R., "Microtips Fluorescent Display," technical digest of IEDM 91, pp. 197-200, 1991			
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(Use several sheets if necessary)ATTY. DOCKET NO.
500466.02APPLICATION NO.
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APPLICANT(S)

Kie Y. Ahn and Leonard Forbes

FILING DATE

November 26, 2001

GROUP ART UNIT

2879

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
KJR	AA	US 6,277,765 B1	08/21/01	Cheng et al.	438	773	
KJR	AB	US 6,333,215 B1	12/25/01	Matsuda et al.	438	149	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AK							
	AL							
	AM							
	AN							
	AO							

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AP	
	AQ	

EXAMINER

Kenneth Ramsey

DATE CONSIDERED

10/23/03

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